

**Списък на публикациите
на гл. ас. д-р Цветан Емилов Иванов**

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“Електрофизични изследвания на тънки слоеве SiO₂ израснати върху поликристален силиций и на полиметилметакрилат, обработени с йонна имплантация за приложение в широкоплощната микроелектроника.” - Автореферат

От тях:

- 1 автореферат на дисертация (№ 41)

- 29 публикации в международни списания с импакт фактор (IF)/ импакт ранк (SJR) - № 1,2, 4-11, 14, 17-22, 25-28, 31-33, 35-37, 39-40

Използвани в дисертационния труд – 6 бр. - № 16, 18, 20, 21, 31, 35